

Supporting Information

Optical anisotropy in van der Waals heterostructures integrated with low symmetry layered compound Nb₄P₂S₂₁

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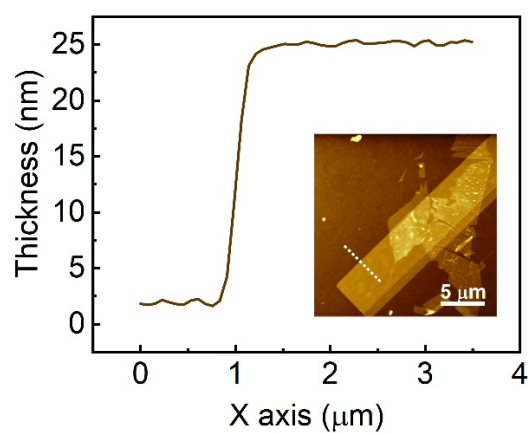


Figure S1. AFM characterization of the device

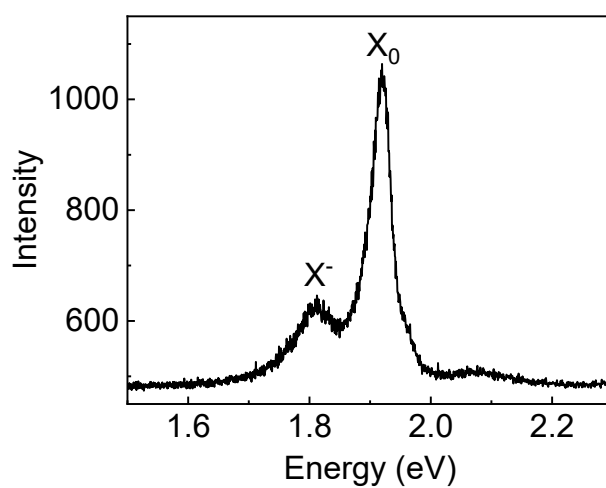


Figure S2. PL spectrum of $\text{MoS}_2/\text{Nb}_4\text{P}_2\text{S}_{21}$ heterostructure collected at 1.8 K and 0 T.

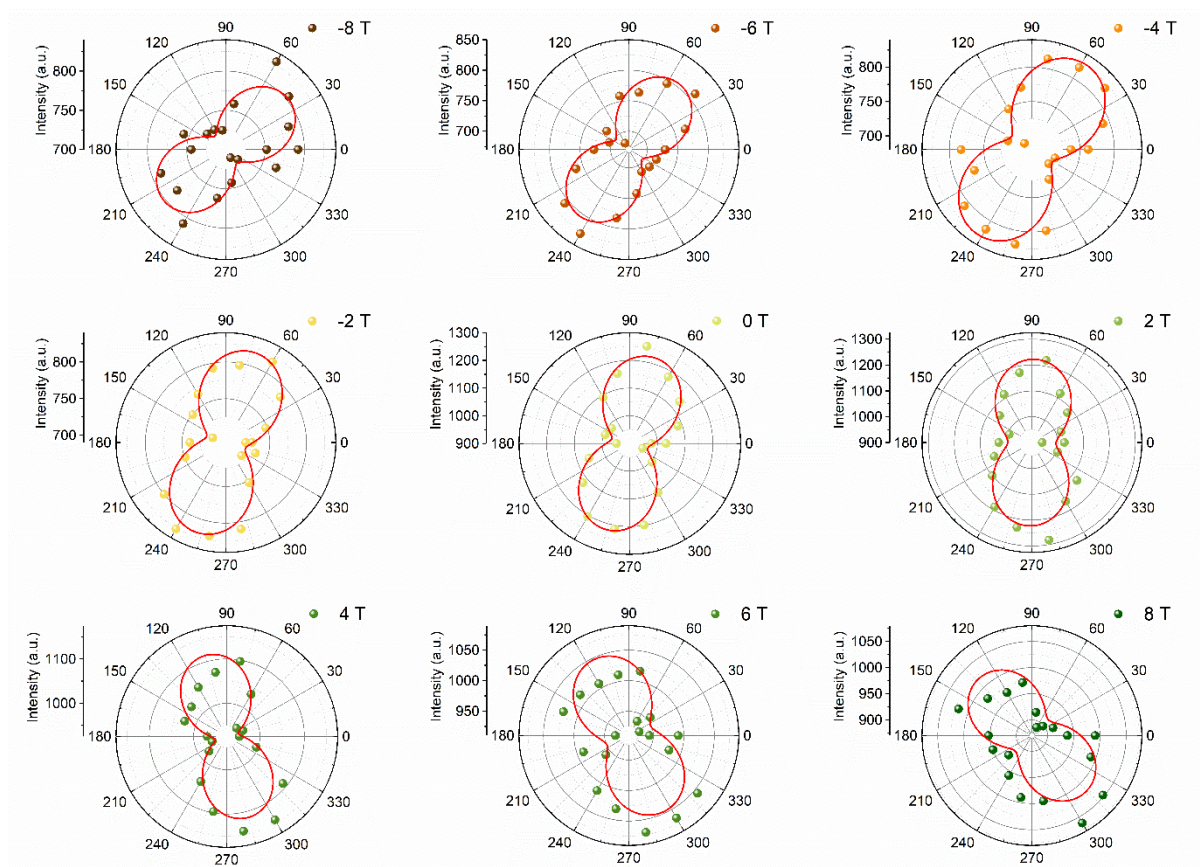


Figure S3. Polarized PL spectra of heterostructure under different magnetic fields from -8 T to +8 T with 2 T step.

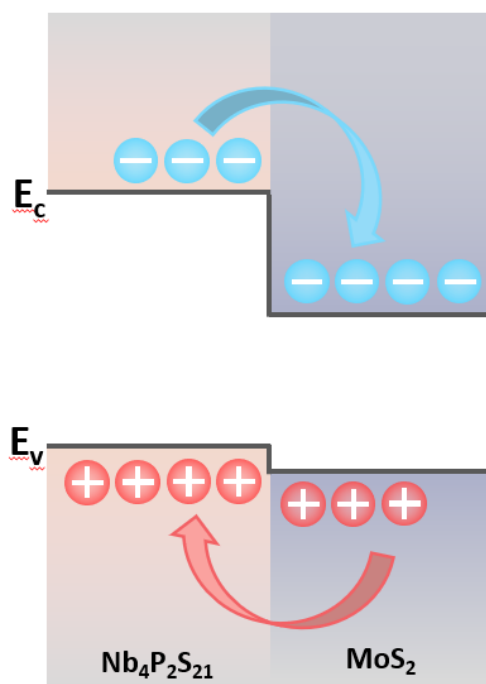


Figure S4. Band alignment of the $\text{MoS}_2/\text{Nb}_4\text{P}_2\text{S}_{21}$ heterostructure. The arrows indicate charge transfer between two materials at their interface.